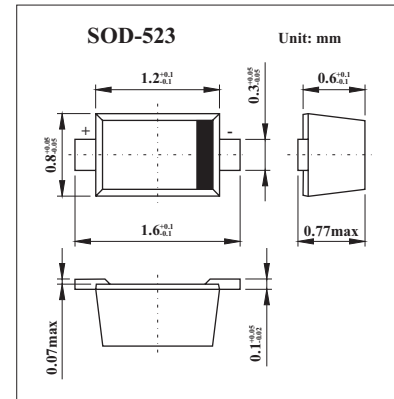


RF PIN Diode

BAR65V-02V

■ Features

- Space saving SOD523 package with low series inductance
- Very small reverse capacitance
- Small reverse capacitance



■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Value	Unit
Reverse voltage	V_R	30	V
Forward current	I_F	100	mA
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C
Junction soldering point	R_{thJS}	100	K/W

■ Electrical Characteristics Ta = 25 °C

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse voltage	V_R	$I_R = 10 \mu A$	30			V
Reverse current	I_R	$V_R = 20 V$			20	nA
Forward voltage	V_F	$I_F = 100 mA$			1.1	V
Diode capacitance	C_D	$f = 1 MHz, V_R = 0$		0.65		pF
		$f = 1 MHz, V_R = 1 V$		0.55	0.9	
		$f = 1 MHz, V_R = 3 V$		0.50	0.8	
Forward resistance	r_f	$f = 100 MHz, I_F = 1 mA$		1		Ω
		$f = 100 MHz, I_F = 5 mA$		0.6	0.95	
		$f = 100 MHz, I_F = 10 mA$		0.52	0.9	
Charge carrier life time	t_{rr}	$I_F = 10 mA, I_R = 6 mA, i_R = 3 mA$		150		ns

■ Marking

Marking	E